

GN4014ZB4LD, GN4014ZB4LS, GN4014ZB4LM

Silicon IGBT Ignition Coil Driver

REJ03G1249-0200

Rev.2.00

Jul. 14, 2005

Features

- Including Clamping Zener
- Low saturation Voltage
 $V_{CE(sat)} = 1.4 \text{ V (typ)}$
- SMD package
LDBPAK

Outline

RENESAS Package code: PRSS0004AE-A
(Package name: LDBPAK(L))

RENESAS Package code: PRSS0004AE-B
(Package name: LDBPAK(S)-(1))

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	370	V
Gate to Emitter voltage	V_{GES}	± 20	V
Emitter to Collector voltage	V_{ECS}	24	V
Collector current	I_C	14	A
Collector peak current	$i_{C(peak)}$	18	A
Collector power dissipation	P_C ^{Note 1}	60	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

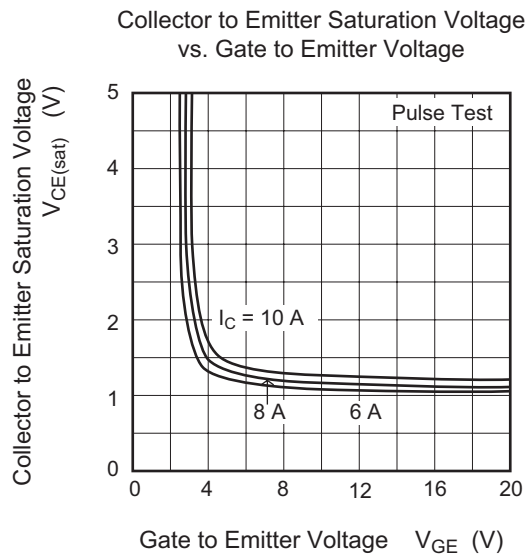
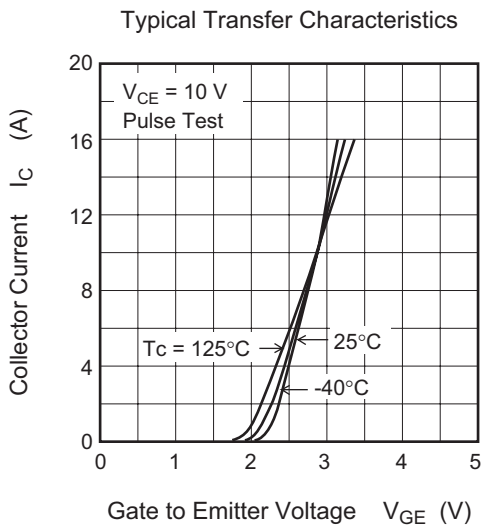
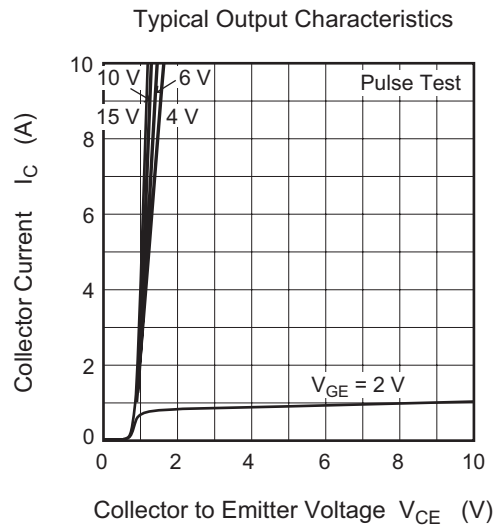
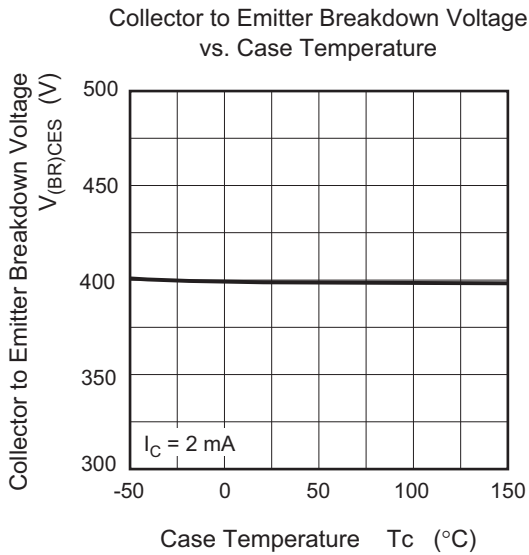
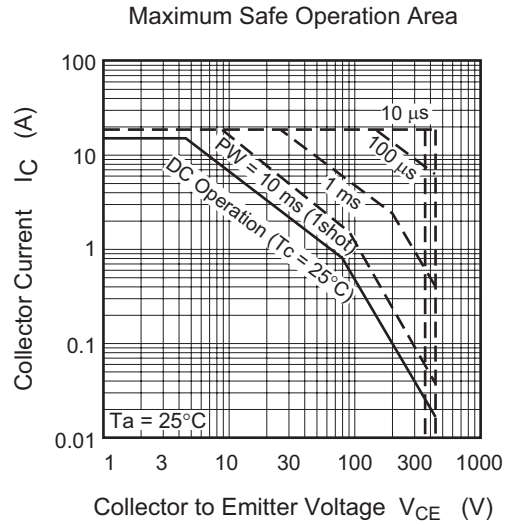
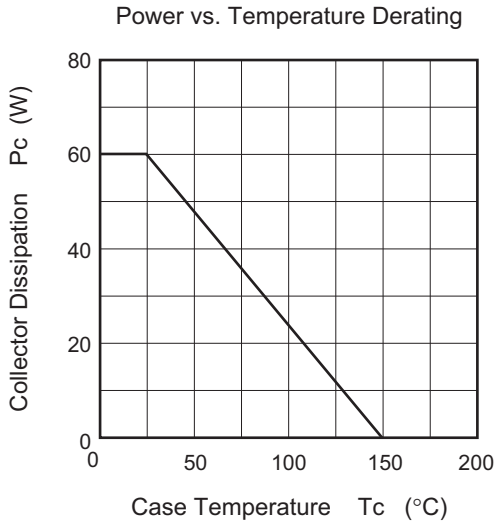
Notes: 1. Value at $T_c = 25^\circ\text{C}$

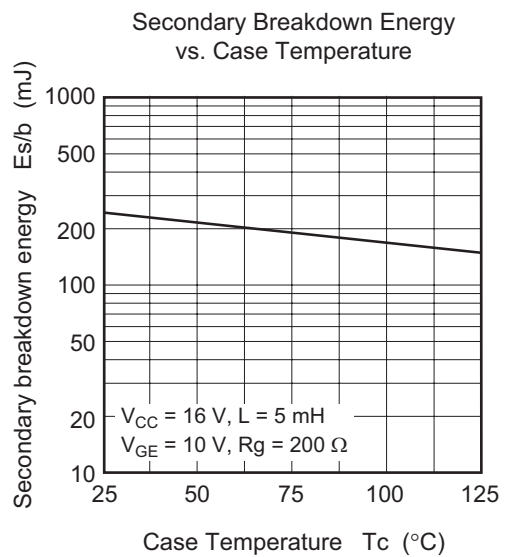
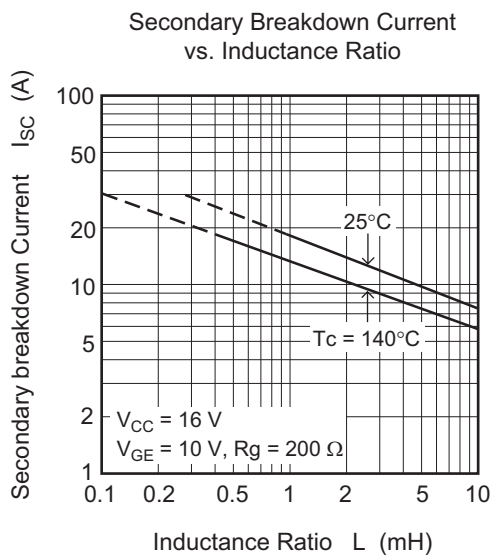
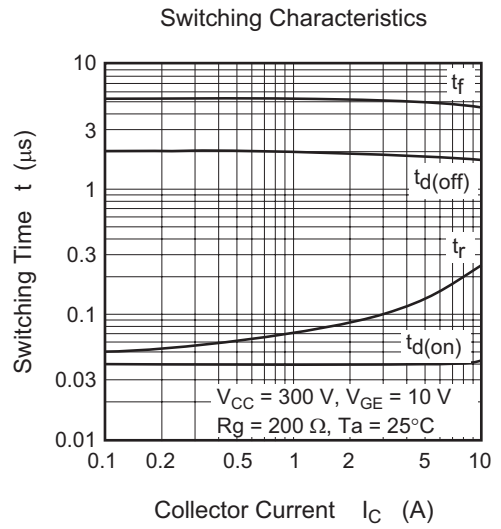
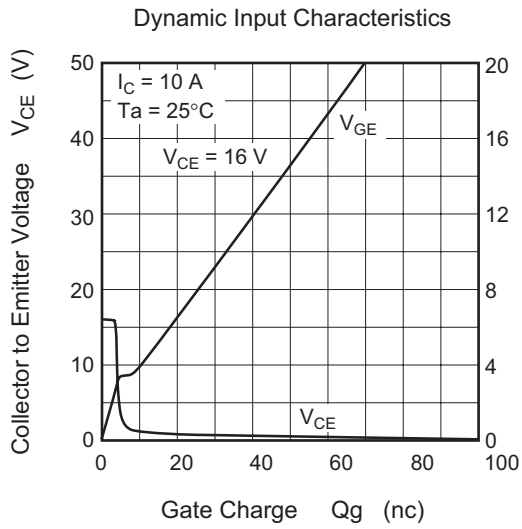
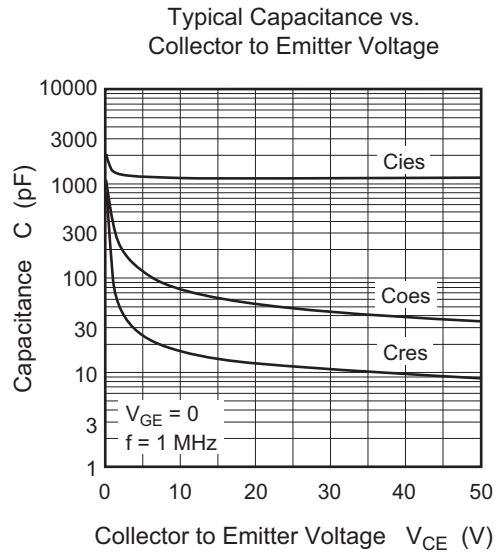
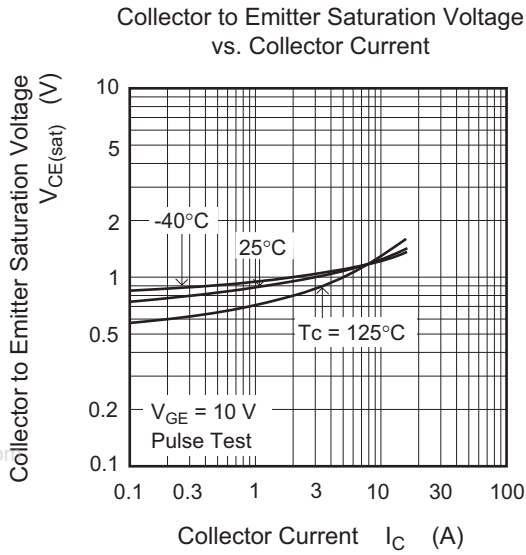
Electrical Characteristics

(Ta = 25°C)

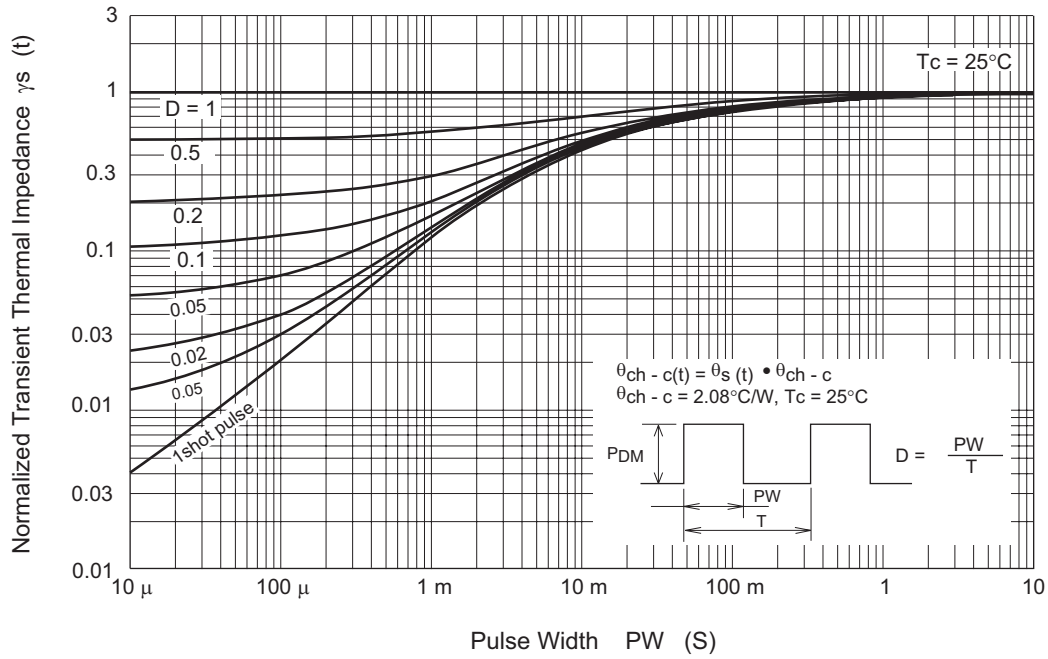
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector to Emitter breakdown voltage	$V_{(BR)CES}$	370	400	430	V	$I_C = 2 \text{ mA}$, $V_{GE} = 0 \text{ V}$
Gate to Emitter breakdown voltage	$V_{(BR)GES}$	± 20	—	—	V	$I_G = \pm 100 \mu\text{A}$, $V_{CE} = 0 \text{ V}$
Collector cutoff current	I_{CES}	—	—	100	μA	$V_{CE} = 300 \text{ V}$, $V_{GE} = 0 \text{ V}$
Gate cutoff current	I_{GES}	—	—	± 100	μA	$V_{GE} = \pm 20 \text{ V}$, $V_{CE} = 0 \text{ V}$
Collector to emitter saturation voltage	$V_{CE(sat)1}$	—	1.4	1.7	V	$I_C = 8 \text{ A}$, $V_{GE} = 10 \text{ V}$
Collector to emitter saturation voltage	$V_{CE(sat)2}$	—	1.6	2.2	V	$I_C = 8 \text{ A}$, $V_{GE} = 4 \text{ V}$
Gate to emitter cutoff voltage	$V_{GE(off)}$	1.3	—	2.2	V	$I_C = 1 \text{ mA}$, $V_{CE} = 10 \text{ V}$
Turn-on delay time	$t_{d(on)}$	—	0.2	—	μs	$V_{CE} = 300 \text{ V}$, $R_L = 50 \Omega$, $V_{GE} = 5 \text{ V}$, $R_G = 200 \Omega$
Rise time	t_r	—	0.4	—	μs	
Turn-off delay time	$t_{d(off)}$	—	1.0	—	μs	
Fall time	t_f	—	5	—	μs	
Input capacitance	C_{iss}	—	1110	—	pF	$V_{CE} = 10 \text{ V}$, $V_{GE} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	75	—	pF	
Reveres transfer capacitance	C_{res}	—	18	—	pF	
Secondary breakdown energy	$E_{s/b}$	230	—	—	mJ	$L = 5 \text{ mH}$

Main Characteristics

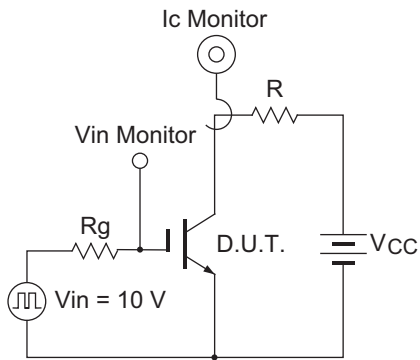




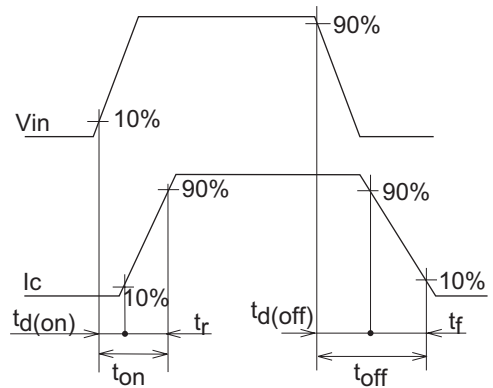
Normalized Transient Thermal Impedance vs. Pulse Width



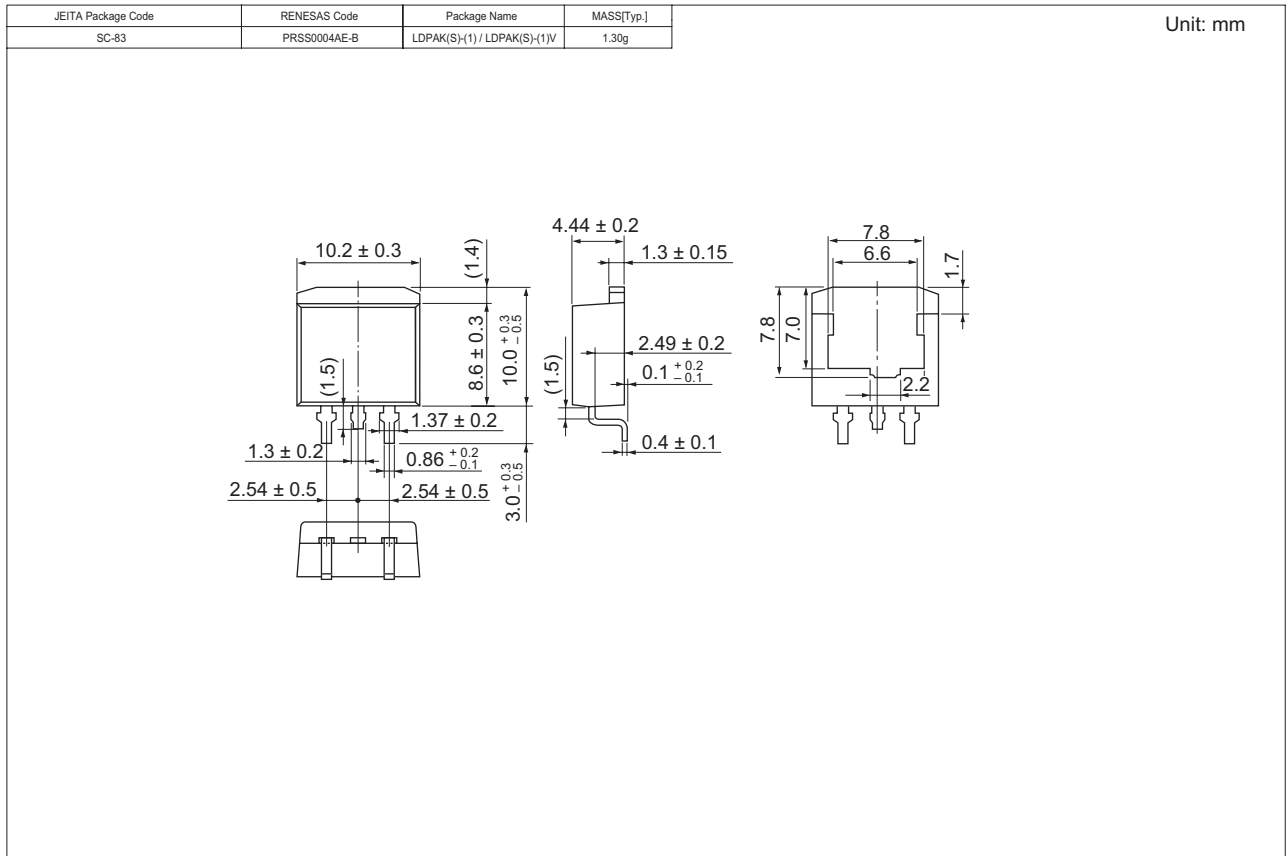
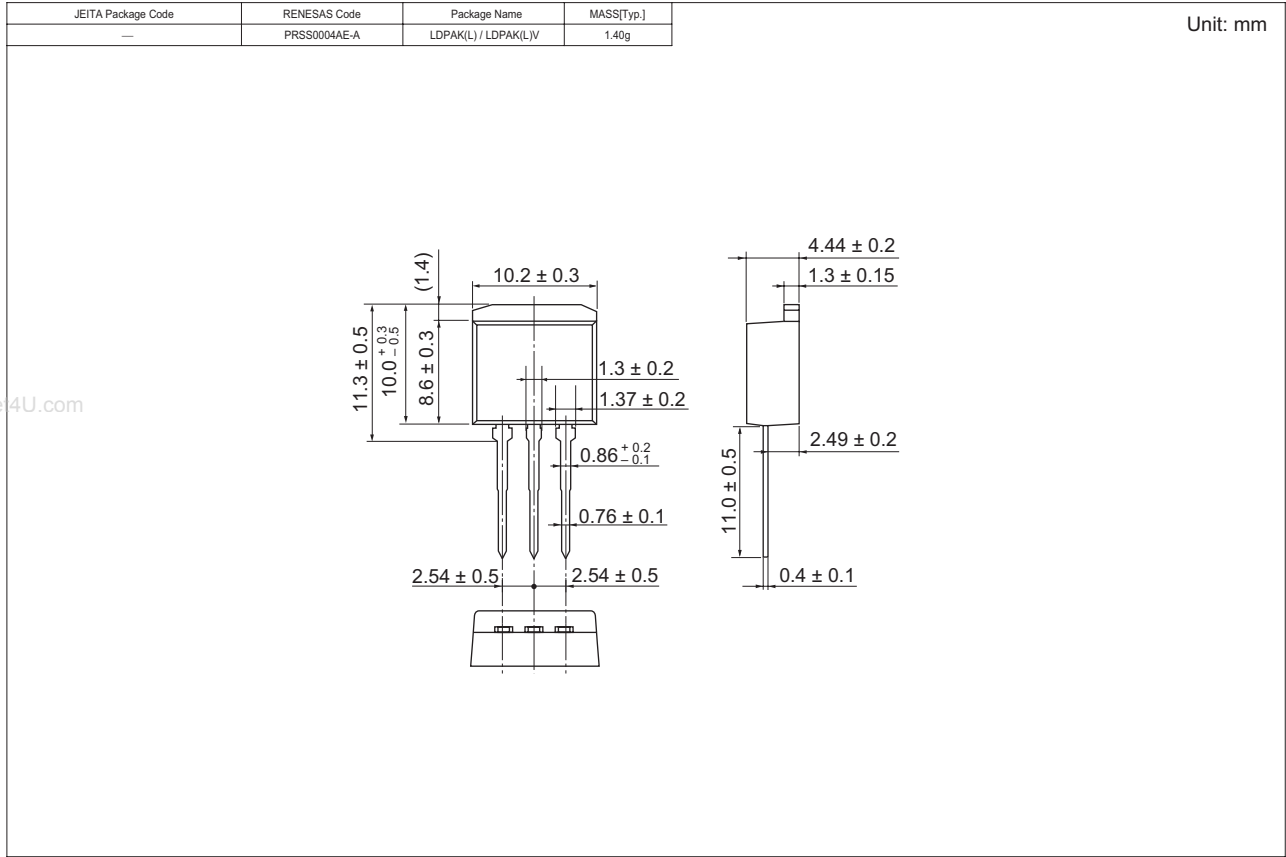
Switching Time Test Circuit



Waveform



Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
GN4014ZB4LD	50 pcs.	Sack
GN4014ZB4LS	1000 pcs.	Taping
GN4014ZB4LM	1000 pcs.	Taping

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450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

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Renesas Technology Hong Kong Ltd.

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Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
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Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510